

REMARKS

Claim 1 was rejected under Section 102 based on Parkinson.

Claim 1 calls for forming a phase change memory element to be read with a voltage greater than or equal to the threshold voltage of the element. Clearly, the threshold voltage being referred to is that of the memory element itself.

The cited reference to Parkinson teaches a memory that includes a memory element 130 and a select device 120 and a second select device 125. A select device is not the same thing as the memory element. The select device is used to select the memory element.

The material cited at the bottom of page 3 and the top of page 4 of Parkinson is talking about the threshold voltage of the select device being exceeded. Of course, that voltage must be exceeded to select the memory element by turning on the select device.

Exceeding the threshold voltage of the select device does not meet the claim element of using a read voltage greater than or equal to the threshold voltage of the memory element itself. To the contrary, the cited reference to Parkinson explicitly teaches away by stating as follows:

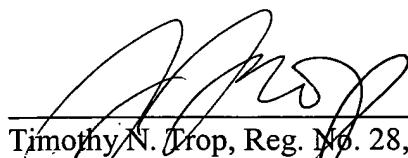
A forced voltage is less than the voltage that will exceed the threshold of the memory element, yet great enough to result in detectably more current through a set bit than a reset bit.

Column 4, lines 38-40 [Emphasis Added].

Thus, since the cited reference explicitly teaches away from the claimed invention, claim 1 and its dependent claims patentably distinguish over Parkinson. On the same basis, claims 6, 11, and 17 and their dependent claims are also distinguished.

In view of these remarks, the application should now be in condition for allowance.

Respectfully submitted,



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